

# DATA SHEET

## **LLE18100X**

**NPN silicon planar epitaxial  
microwave power transistor**

Product specification

November 1994

# NPN silicon planar epitaxial microwave power transistor

LLE18100X

## FEATURES

- Diffused emitter ballasting resistors providing excellent current sharing and withstanding a high VSWR
- Interdigitated structure provides high emitter efficiency
- Gold metallization realizes very good stability of the characteristics and excellent lifetime
- Multicell geometry gives good balance of dissipated power and low thermal resistance
- Internal input prematching ensures good stability and allows an easier design of wideband circuits.

## DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT437A glued cap metal ceramic flange package, with emitter connected to flange.

## APPLICATIONS

Intended for use in common emitter, class AB power amplifiers in CW conditions for professional applications at 1.85 GHz.

## QUICK REFERENCE DATA

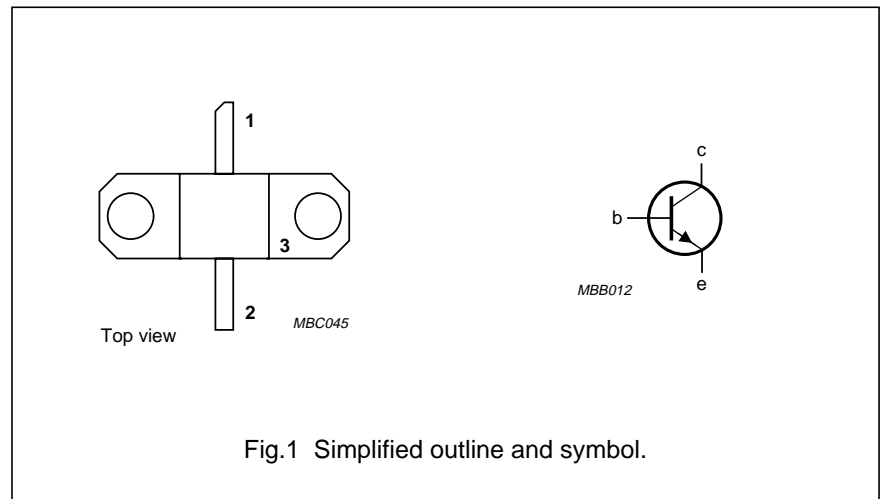
Microwave performance up to  $T_{mb} = 25\text{ }^\circ\text{C}$  in a common emitter class AB amplifier.

MODE OF OPERATION	f (GHz)	V <sub>CE</sub> (V)	I <sub>CQ</sub> (A)	P <sub>L1</sub> (W)	G <sub>po</sub> (dB)	Z <sub>i</sub> /Z <sub>L</sub> (Ω)
class AB (CW)	1.85	24	0.1	≥ 9	≥ 8	see Figs 8 and 9

## PINNING - SOT437A

PIN	DESCRIPTION
1	collector
2	base
3	emitter connected to flange

## PIN CONFIGURATION



## WARNING

**Product and environmental safety - toxic materials**

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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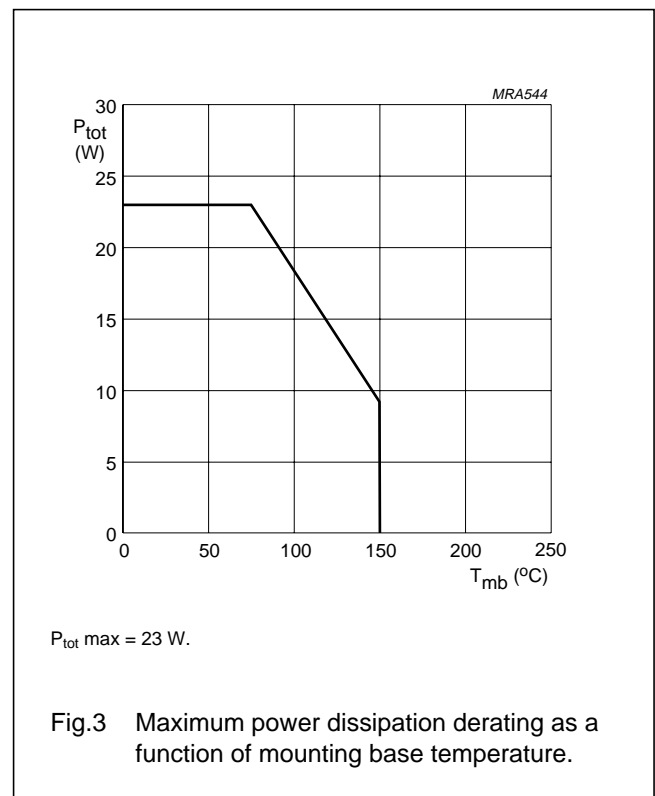
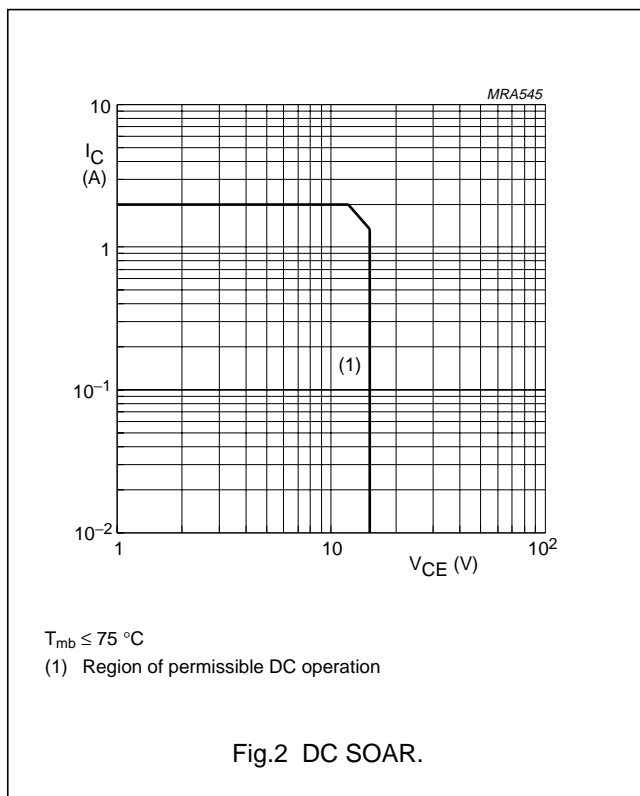
## LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	45	V
$V_{CER}$	collector-emitter voltage	$R_{BE} = 220 \Omega$	–	30	V
$V_{CEO}$	collector-emitter voltage	open base	–	15	V
$V_{EBO}$	emitter-base voltage	open collector	–	3	V
$I_C$	collector current		–	2	A
$P_{tot}$	total power dissipation	$T_{mb} = 75 \text{ }^\circ\text{C}$	–	23	W
$T_{stg}$	storage temperature range		–65	150	$^\circ\text{C}$
$T_j$	junction temperature		–	200	$^\circ\text{C}$
$T_{sld}$	soldering temperature	$t \leq 10 \text{ s}$ note 1	–	235	$^\circ\text{C}$

### Note

- Up to 0.2 mm from ceramic.



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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 100\ ^\circ\text{C}$	4.2 K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink		0.2 K/W

## CHARACTERISTICS

$T_{mb} = 25\ ^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$V_{CB} = 20\ \text{V};$ $I_E = 0$	–	1	mA
$I_{CER}$	collector cut-off current	$V_{CE} = 30\ \text{V};$ $R_{BE} = 220\ \Omega$	–	10	mA
$I_{CEO}$	collector cut-off current	$V_{CE} = 20\ \text{V};$ $I_B = 0$	–	10	mA
$I_{EBO}$	emitter cut-off current	$V_{EB} = 1.5\ \text{V};$ $I_C = 0$	–	100	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 3\ \text{V};$ $I_C = 1\ \text{A}$	15	100	

## APPLICATION INFORMATION

Microwave performance up to  $T_{mb} = 25\ ^\circ\text{C}$  in a common emitter class AB amplifier (note 1).

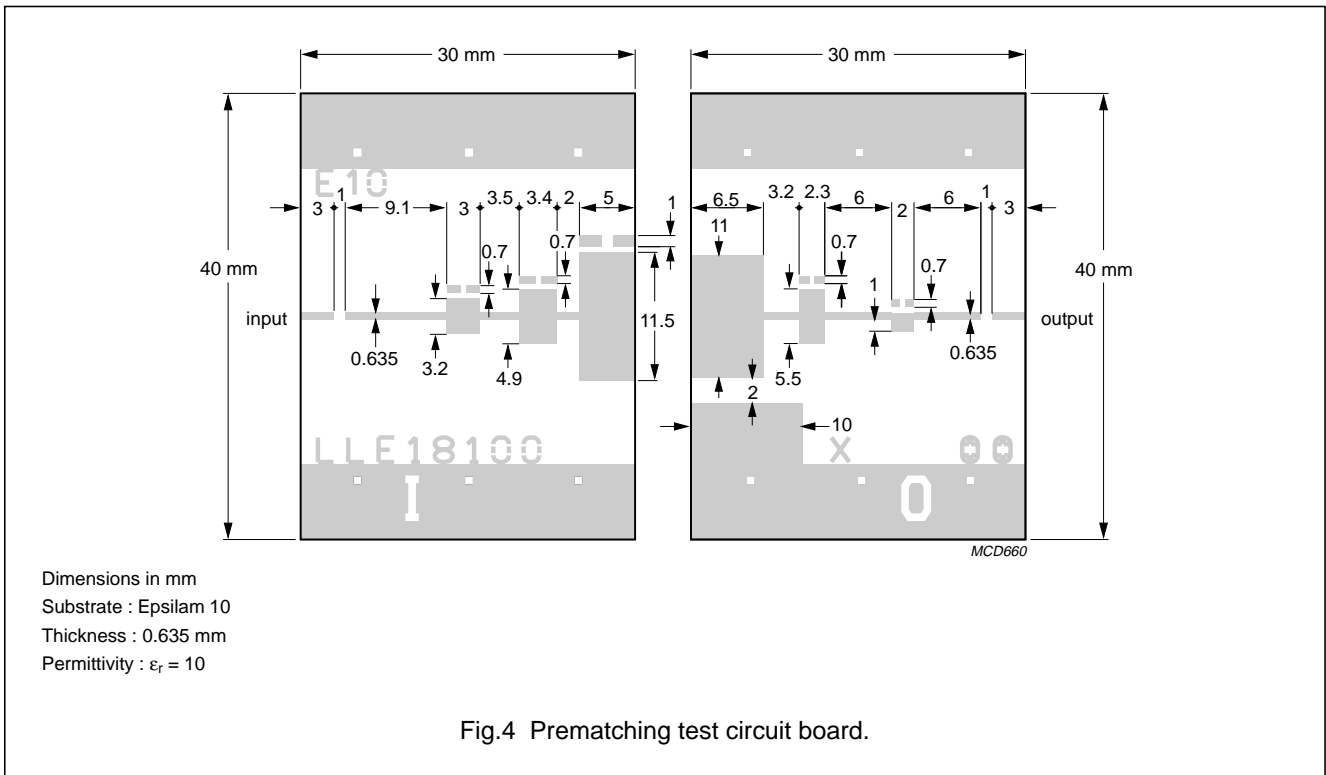
MODE OF OPERATION	f (GHz)	$V_{CE}$ (V)	$I_{CQ}$ (A)	$P_{L1}$ (W)	$G_{po}$ (dB)	$Z_i/Z_L$ ( $\Omega$ )
class AB (CW)	1.85	24	0.1	$\geq 9;$ typ. 11	$\geq 8;$ typ. 10	see Figs 8 and 9

### Note

- The test circuit is split into 2 independant halves each being  $30 \times 40\ \text{mm}$  in size.

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List of components (see bias circuit)

COMPONENT	DESCRIPTION	VALUE	CATALOGUE NO.
TR1	transistor, BDT85 (or equivalent)		
D1	diode, BY239800 (or equivalent) note 1		
D2	diode, BY239800 note 2		
R1	resistor	100 $\Omega$	
R2	resistor	3.3 k $\Omega$	
R3	resistor	56 $\Omega$	
P1	potentiometer, 10 turns (sfernice)	4.7 k $\Omega$	
C1	electrolytic capacitor	10 $\mu$ F, 40 V	
C5, C6	feedthrough bypass capacitor	1500 pF	Erie, ref. 1250-003
L1	5 turns 0.5 mm copper wire with ferrite bead		
L2	5 turns 0.5 mm copper wire		

Notes

1. In thermal contact with TR1.
2. In thermal contact with D.U.T.

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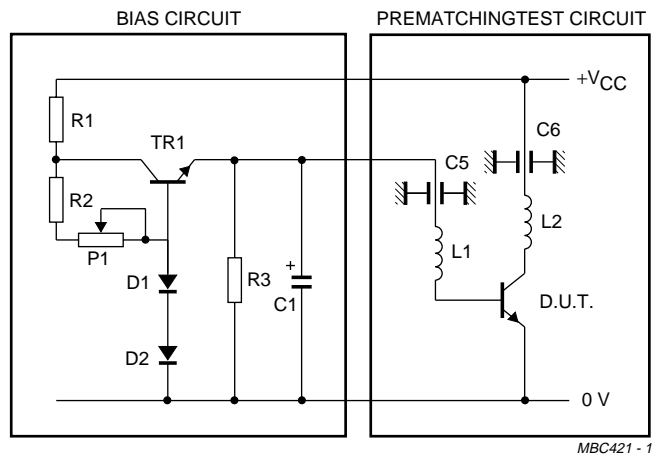
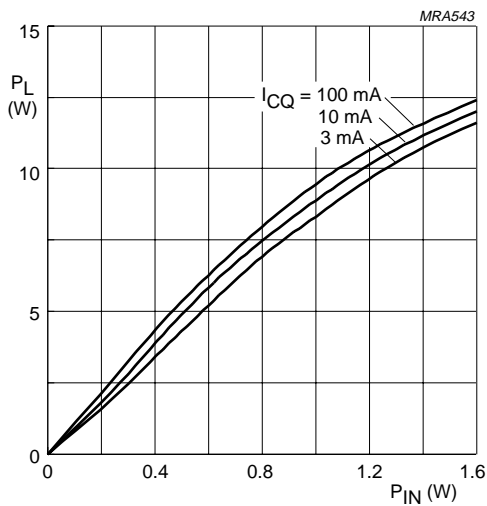
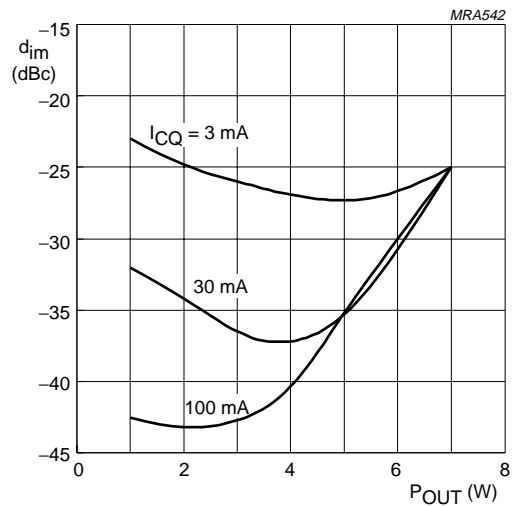


Fig.5 Class AB bias circuit at 1.85 GHz.



$V_{CE} = 24\text{ V}$   
 $f = 1.85\text{ GHz}$

Fig.6 Load power as a function of input power.

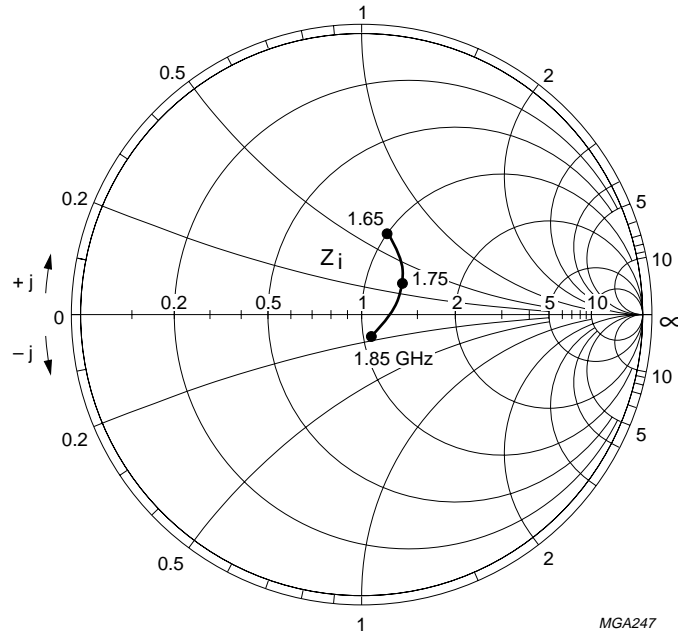


$V_{CE} = 24\text{ V}$   
 $f = 1.85\text{ GHz}$

Fig.7 Intermodulation distortion as a function of average output power.

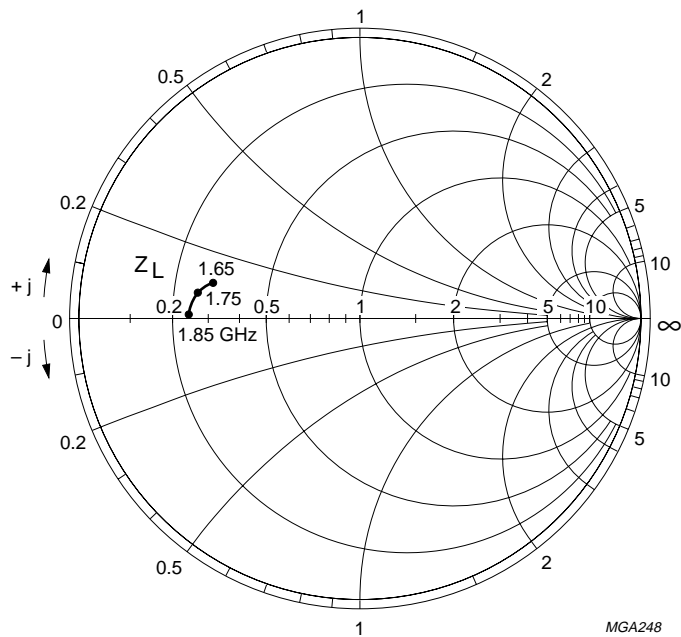
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$V_{CE} = 24 \text{ V};$   
 $Z_0 = 10 \Omega;$   
 $I_{CQ} = 0.1 \text{ A}.$

Fig.8 Input impedance as a function of frequency; typical values.



$V_{CE} = 24 \text{ V};$   
 $Z_0 = 10 \Omega;$   
 $I_{CQ} = 0.1 \text{ A}.$

Fig.9 Optimum load impedance as a function of frequency; typical values.

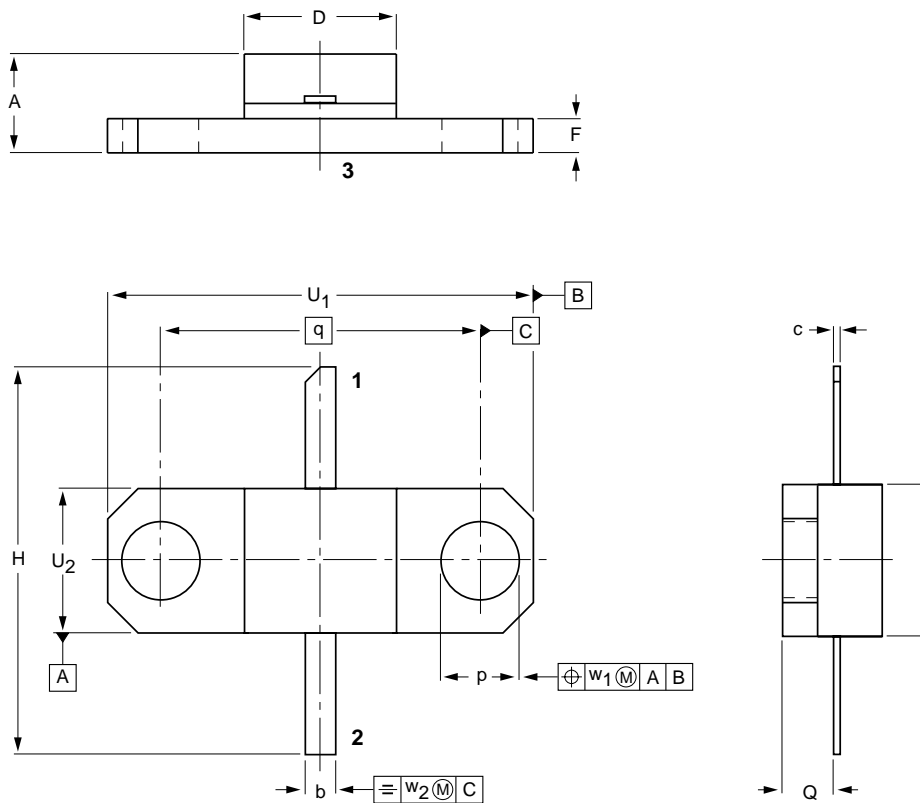
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PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 2 leads

SOT437A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	E	F	H	p	Q	q	U <sub>1</sub>	U <sub>2</sub>	w <sub>1</sub>	w <sub>2</sub>
mm	5.03 4.31	1.66 1.39	0.13 0.07	6.99 6.22	6.99 6.22	1.66 1.39	17.02 16.00	3.43 3.17	2.29 2.03	14.22	19.03 18.77	6.48 6.22	0.51	1.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT437A						97-05-23



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**LLE18100X****DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

**LIFE SUPPORT APPLICATIONS**

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